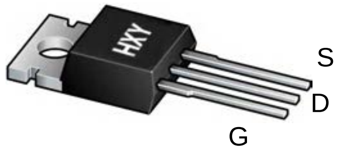
IRFB4410ZPBF

N-SGT Enhancement Mode MOSFET

Description

The IRFB4410ZPBF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



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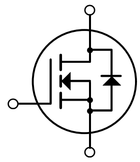
General Features

V_{DS} = 100V I_D = 70A

$R_{DS(ON)}$ < 10.5mΩ @ V_{GS}=10V



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
IRFB4410ZPBF	TO-220	FB4410Z XXXX	50

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain CurrentTC=25 ℃	70	A
I_{DM}	PuledDrainCurrentnote1	280	A
EAS	Single Pulse Avalanche Energy[3]	110	mJ
P_D@T_C=25℃	Total Power Dissipation[4]	100	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{θJA}$	Thermal Resistance Junction-Ambient [1]	64	℃/W
$R_{θJC}$	Thermal Resistance Junction-Ambient [1]	1.25	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.098	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=20A	---	8.5	10.5	mΩ
		V_{GS}=4.5V , I_D=15A	---	9.5	15	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	---	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.57	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=80V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	0.48	---	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=50V , V_{GS}=50V , I_D=10A	---	31.3	---	nC
Q_{gs}	Gate-Source Charge		---	3.49	---	
Q_{gd}	Gate-Drain Charge		---	7.63	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=50V , V_{GS}=10V , R_G=4Ω I_D=10A	---	16	---	ns
T_r	Rise Time		---	10	---	
$T_{d(off)}$	Turn-Off Delay Time		---	40	---	
T_f	Fall Time		---	6	---	
C_{iss}	Input Capacitance	V_{DS}=50V , V_{GS}=0V , f=1MHz	---	1368	---	pF
C_{oss}	Output Capacitance		---	451	---	
C_{rss}	Reverse Transfer Capacitance		---	12.9	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	70	A
I_{SM}	Pulsed Source Current[2,5]		---	---	280	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=10A , dI/dt=100A/μs , T_J=25℃	---	103	---	nS
Q_{rr}	Reverse Recovery Charge		---	187	---	nC

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

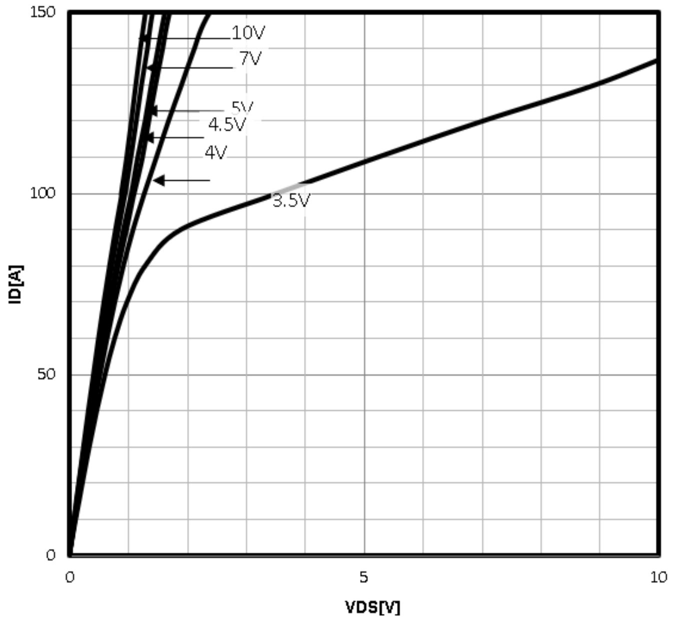
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=11A

4.The power dissipation is limited by 150℃ junction temperature

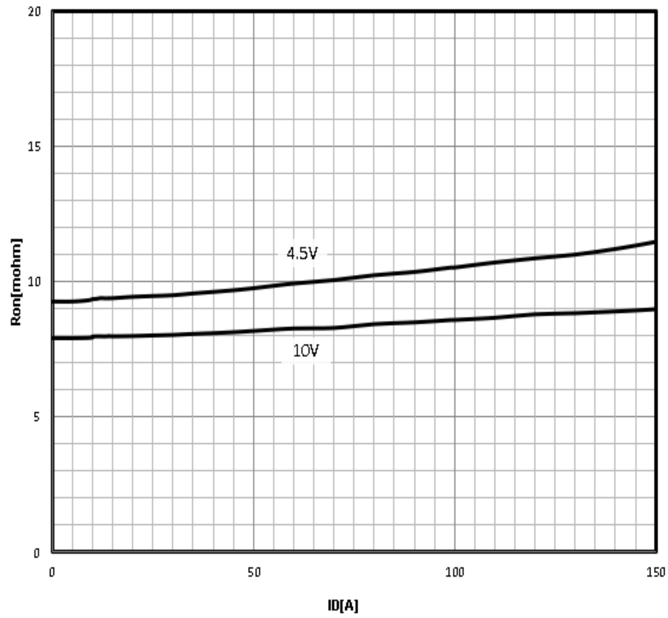
5 .The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

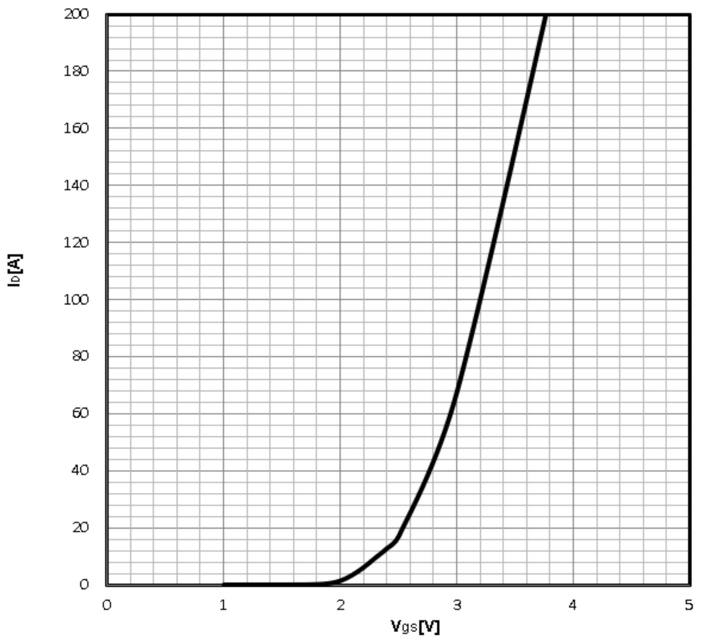
Typ. output characteristics
$I_D=f(V_{DS})$



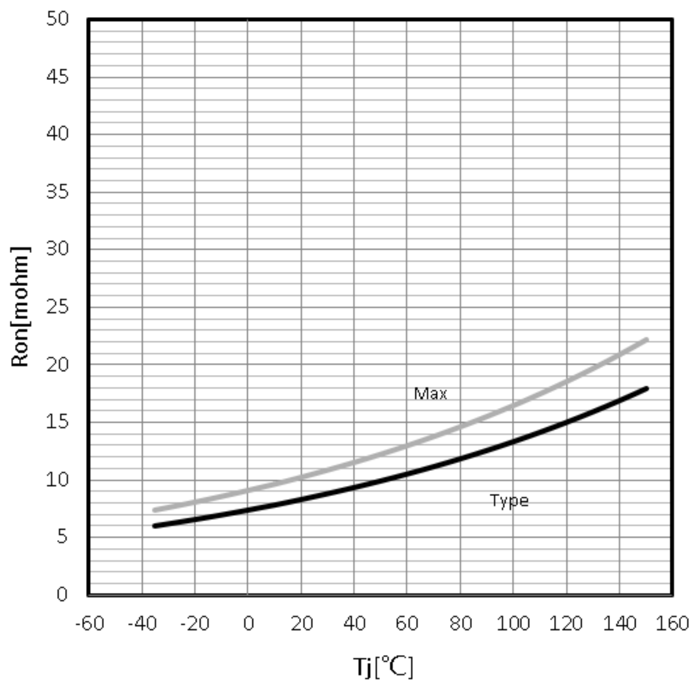
Typ. drain-source on resistance
$R_{DS(on)}=f(I_D)$



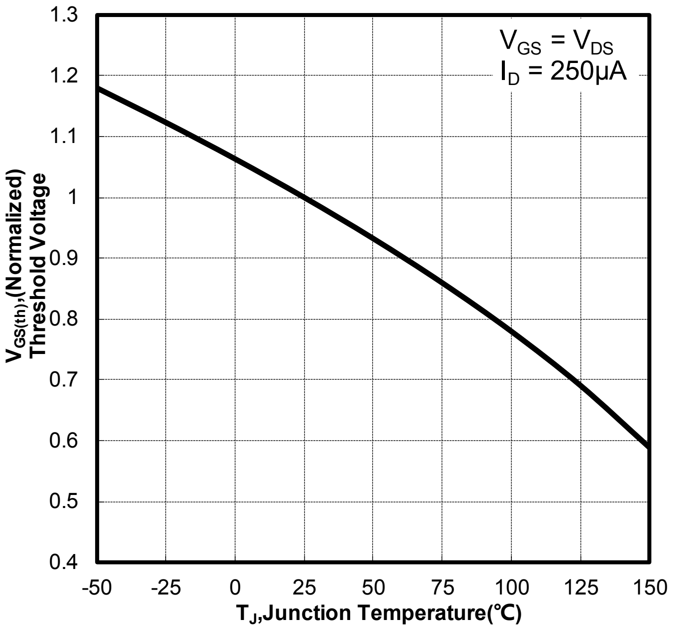
Typ. transfer characteristics
$I_D=f(V_{GS})$



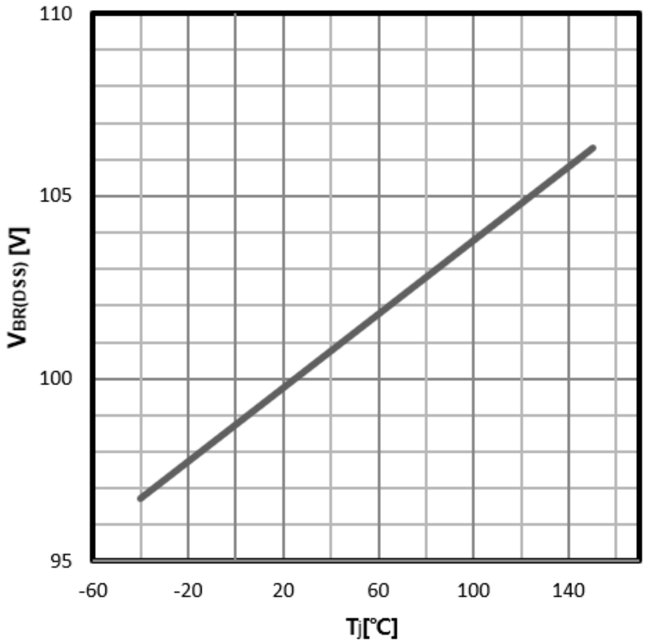
Drain-source on-state resistance
$R_{DS(on)}=f(T_j);I_D=20A;\ V_{GS}=10V$



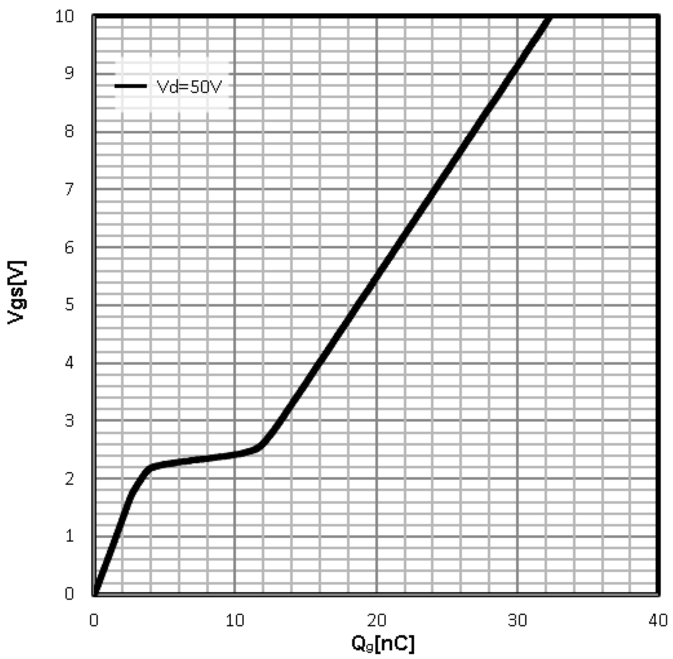
Gate Threshold Voltage
V_{TH}=f(T_j); I_D=250uA



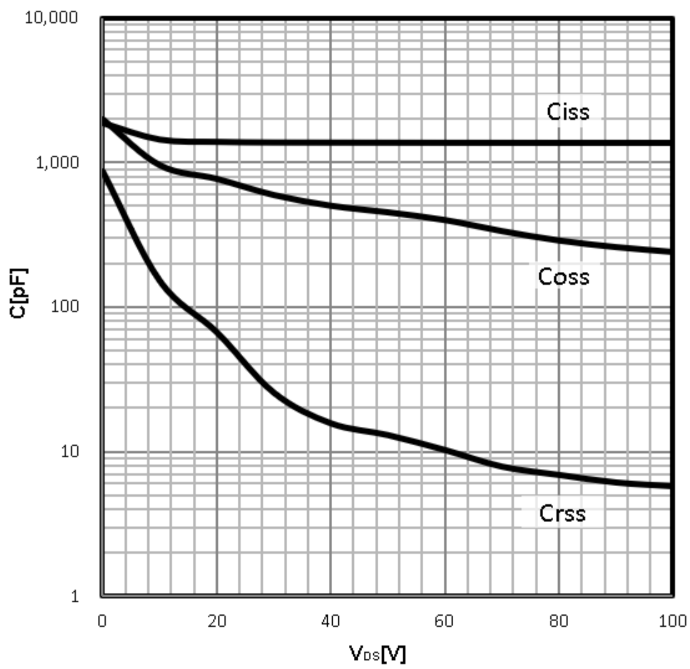
Drain-source breakdown voltage
$V_{BR(DSS)}$=f(T_j); I_D=250uA



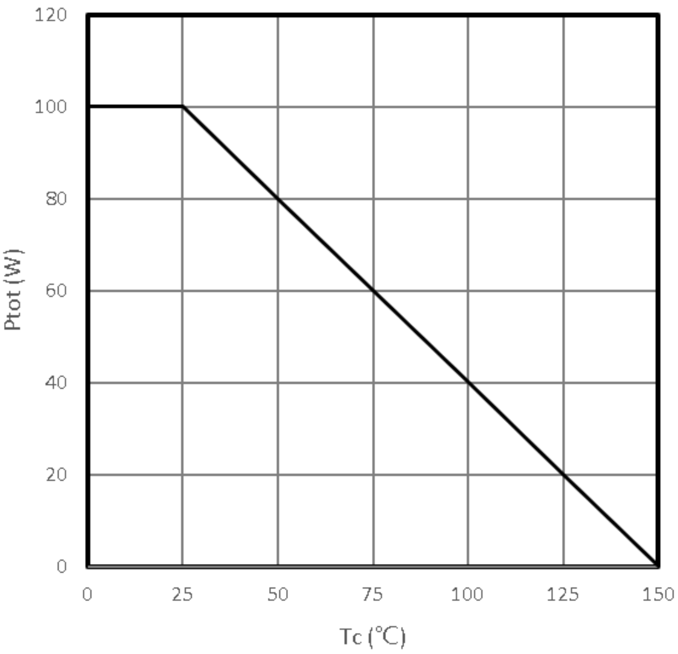
Typ. gate charge
V_{GS}=f(Q_g) ; I_D=10A



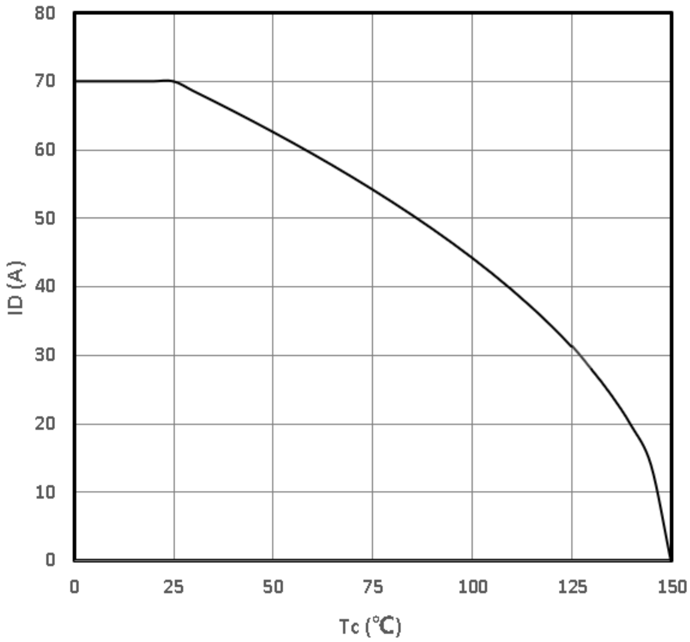
Typ. capacitances
C =f(V_{DS}); V_{GS}=0V; f =1MHz



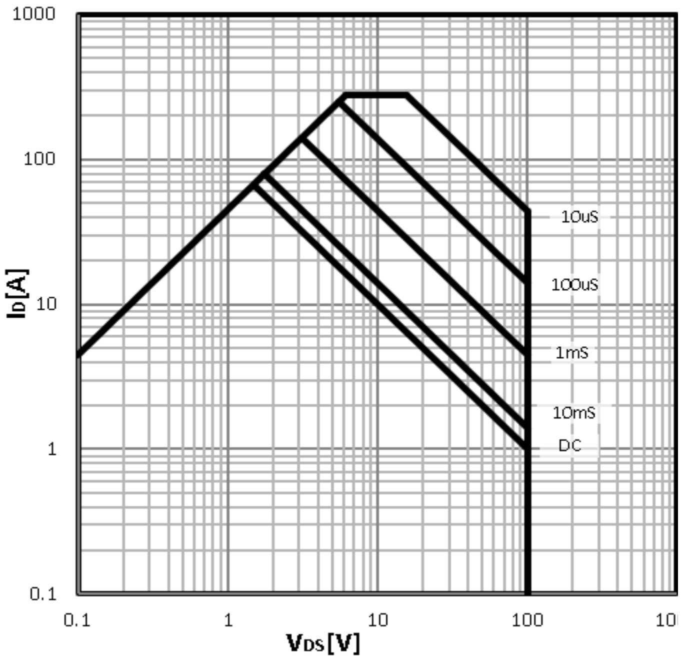
Power Dissipation
$P_{tot}=f(T_C)$



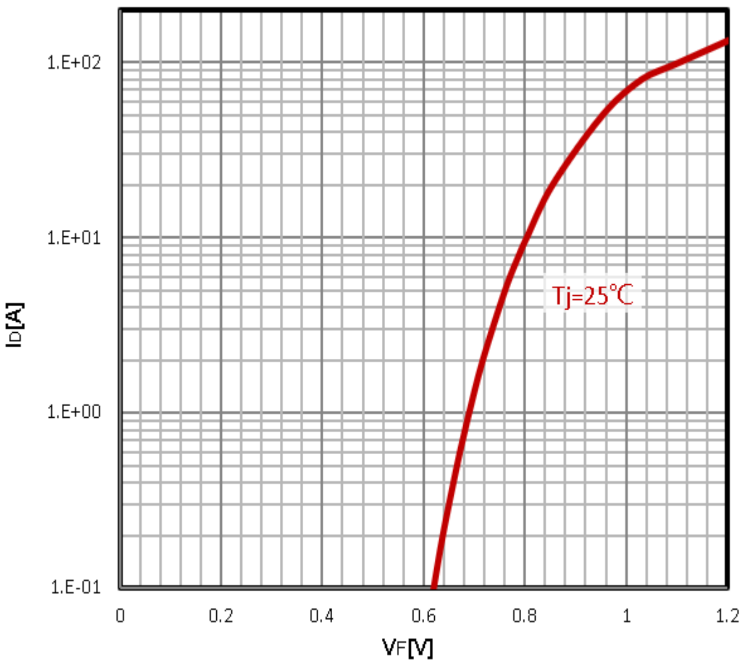
Maximum Drain Current
$I_D=f(T_C)$



Safe operating area
$I_D=f(V_{DS})$

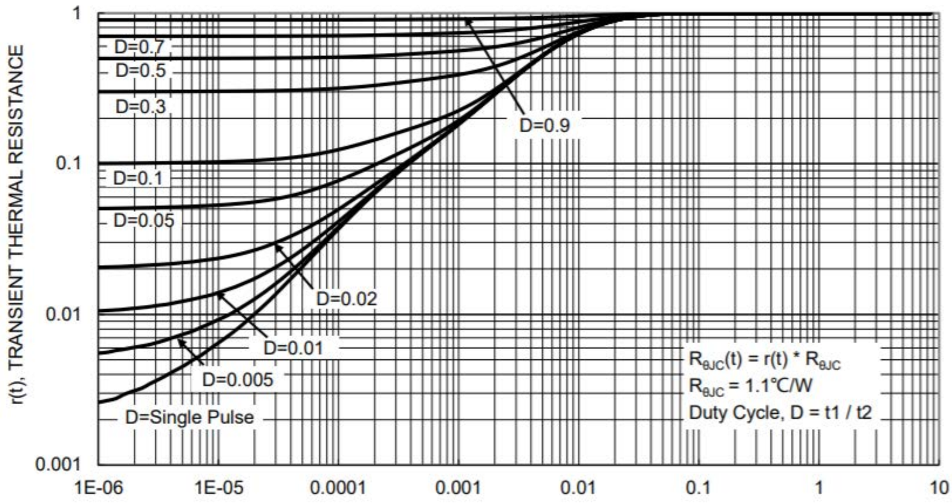


Body Diode Forward Voltage Variation
$I_F=f(V_{GS})$



Max. transient thermal impedance

$Z_{thJC}=f(t_p)$



Package Information

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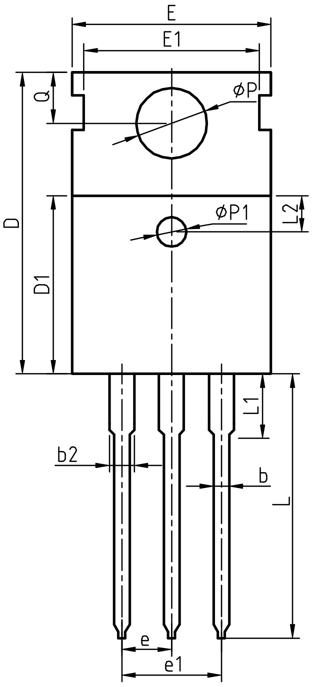

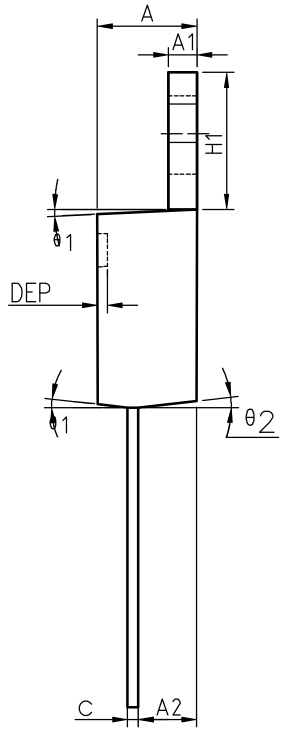

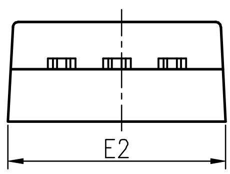

COMMON DIMENSIONS

SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185
A1	1.27	1.30	1.33	0.050	0.051	0.052
A2	2.35	2.40	2.50	0.093	0.094	0.098
b	0.77	0.80	0.90	0.030	0.031	0.035
b2	1.17	1.27	1.36	0.046	0.050	0.054
c	0.48	0.50	0.56	0.019	0.020	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9.10	9.20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
E	9.80	10.00	10.20	0.386	0.394	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.402
e		2.54	BSC		0.100	BSC
e1		5.08	BSC		0.200	BSC
H1	6.40	6.50	6.60	0.252	0.256	0.260
L	12.75	13.50	13.65	0.502	0.531	0.537
L1	-	3.10	3.30	-	0.122	0.130
L2		2.50	REF		0.098	REF
P	3.50	3.60	3.63	0.138	0.142	0.143
P1	3.50	3.60	3.63	0.138	0.142	0.143
Q	2.73	2.80	2.87	0.107	0.110	0.113
θ1	5°	7°	9°	5°	7°	9°
θ2	1°	3°	5°	1°	3°	5°
θ3	1°	3°	5°	1°	3°	5°

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